

FDB082N15A

N-Channel PowerTrench® MOSFET

150V, 105A, 8.2mΩ

Features

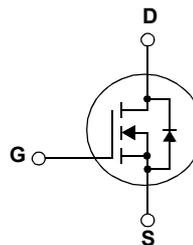
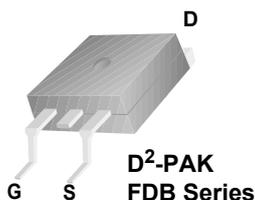
- $R_{DS(on)} = 6.7m\Omega$ (Typ.)@ $V_{GS} = 10V, I_D = 75A$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC to DC Converters
- Synchronous Rectification for Server/Telecom PSU
- Battery Charger
- AC motor drives and Uninterruptible Power Supplies
- Off-line UPS



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	150	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ C$, Silicon Limited)	105
		- Continuous ($T_C = 100^\circ C$, Silicon Limited)	75
I_{DM}	Drain Current	- Pulsed (Note 1)	420
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	542
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0
P_D	Power Dissipation	($T_C = 25^\circ C$)	231
		- Derate above $25^\circ C$	1.54
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

*Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.65	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB082N15A	FDB082N15A	D2-PAK	330mm	24mm	800

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$, $T_C = 25^\circ\text{C}$	150	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.08	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 120\text{V}$, $T_C = 150^\circ\text{C}$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 75\text{A}$	-	6.7	8.20	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 75\text{A}$ (Note 4)	-	139	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	4645	6040	pF
C_{oss}	Output Capacitance		-	1445	1880	pF
C_{rss}	Reverse Transfer Capacitance		-	100	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 75\text{V}$, $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$	-	64.5	84	nC
Q_{gs}	Gate to Source Gate Charge		-	19.1	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	8.7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	13.5	-	nC
ESR	Equivalent Series Resistance(G-S)	Drain Open, $f = 1\text{MHz}$	-	2.5	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{V}$, $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 4.7\Omega$	-	22	54	ns
t_r	Turn-On Rise Time		-	58	126	ns
$t_{d(off)}$	Turn-Off Delay Time		-	61	132	ns
t_f	Turn-Off Fall Time		-	26	62	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	105	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	420	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_{SD} = 75\text{A}$	-	-	1.25	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{V}$, $I_{SD} = 75\text{A}$, $V_{DD} = 120\text{V}$	-	96	-	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$	-	268	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Starting $T_J = 25^\circ\text{C}$, $L = 3\text{ mH}$, $I_{SD} = 19\text{ A}$
3. $I_{SD} \leq 75\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

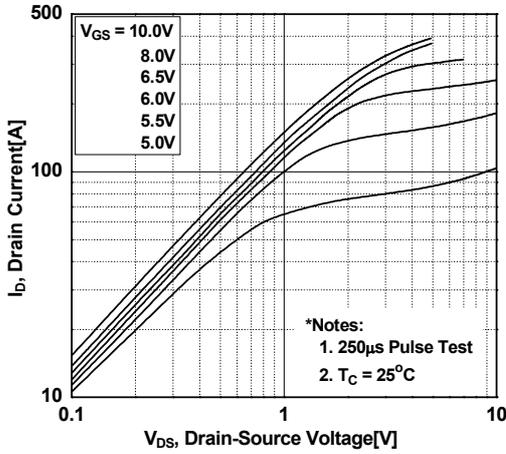


Figure 2. Transfer Characteristics

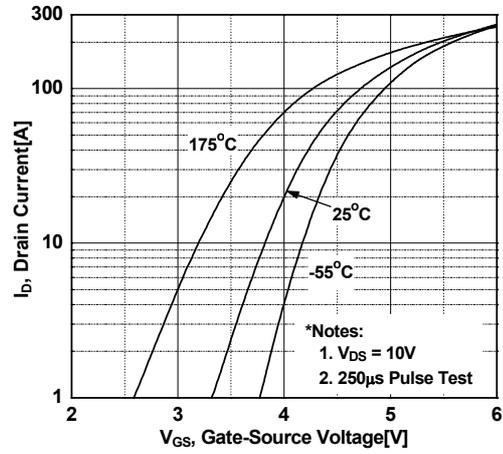


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

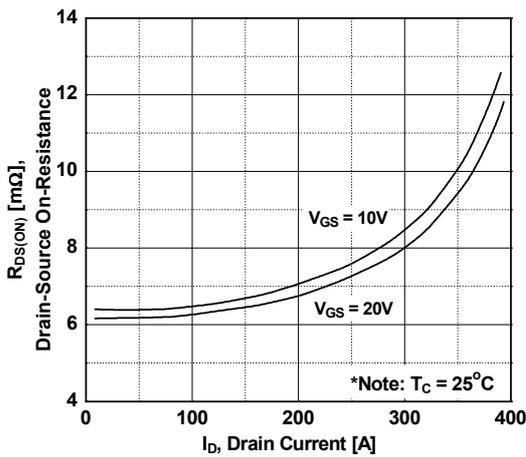


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

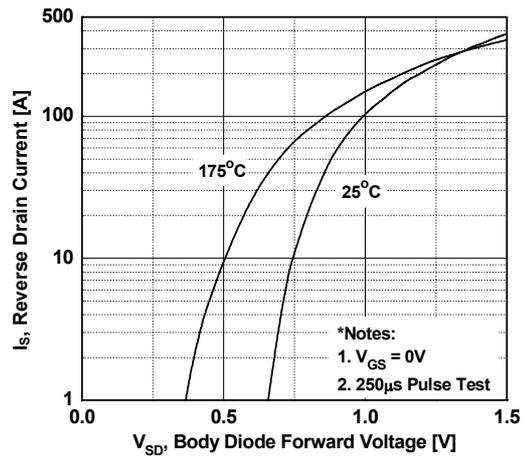


Figure 5. Capacitance Characteristics

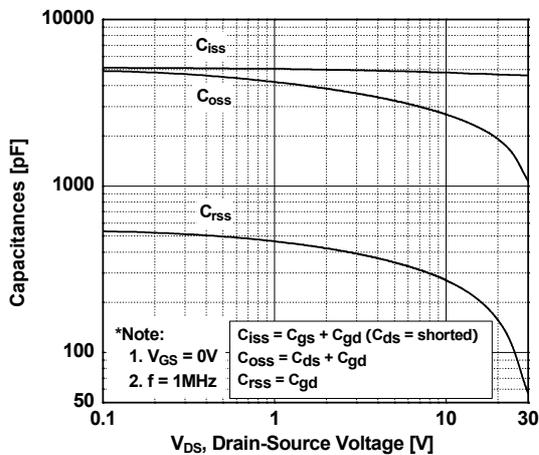
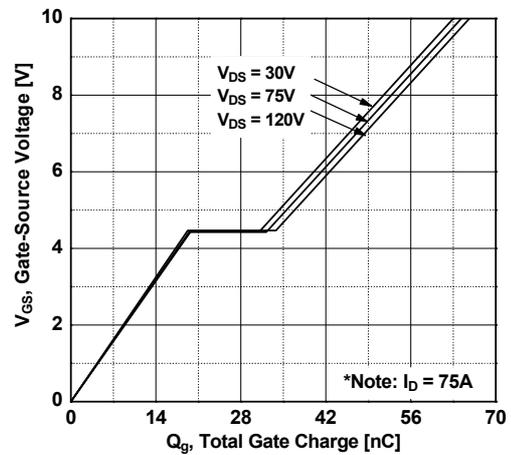


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

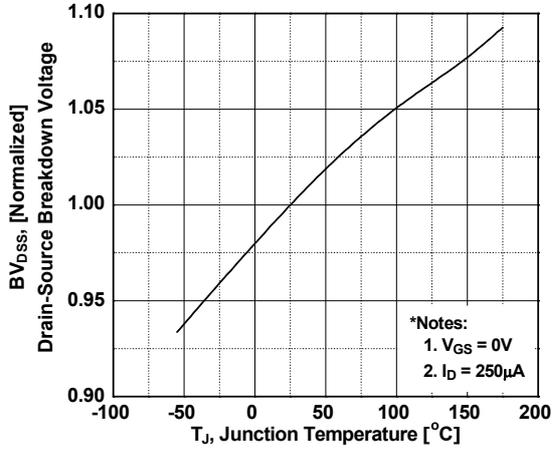


Figure 8. On-Resistance Variation vs. Temperature

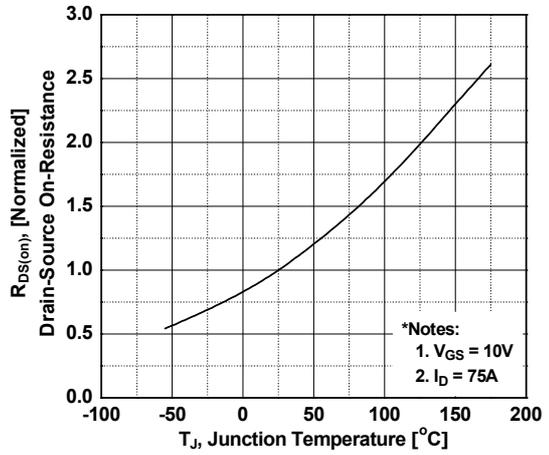


Figure 9. Maximum Safe Operating Area

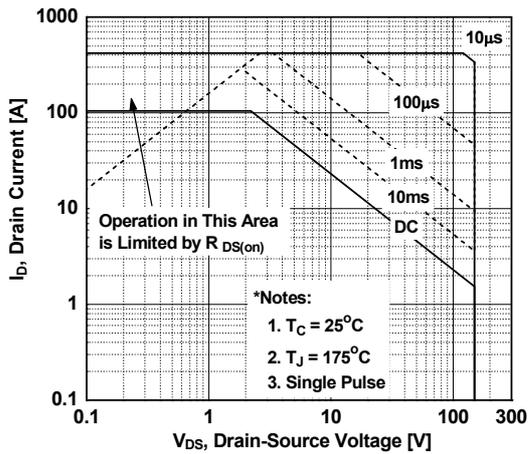


Figure 10. Maximum Drain Current vs. Case Temperature

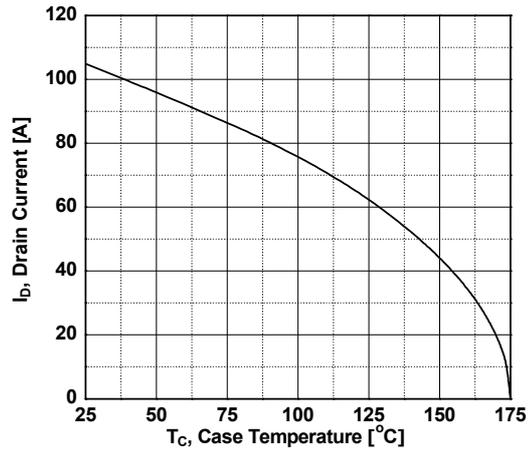
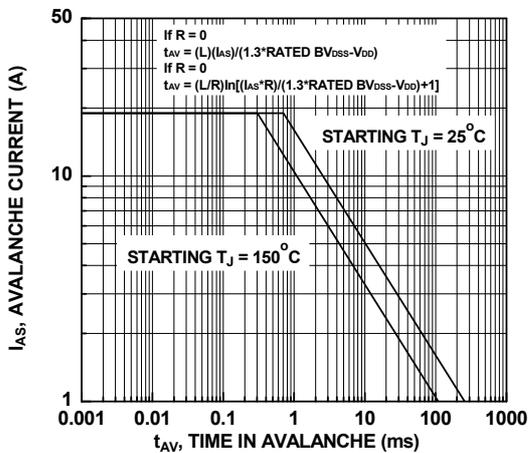
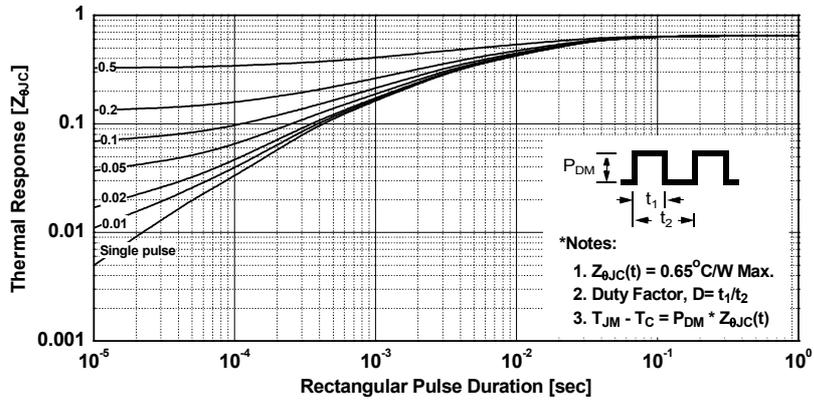


Figure 11. Unclamped Inductive Switching Capability

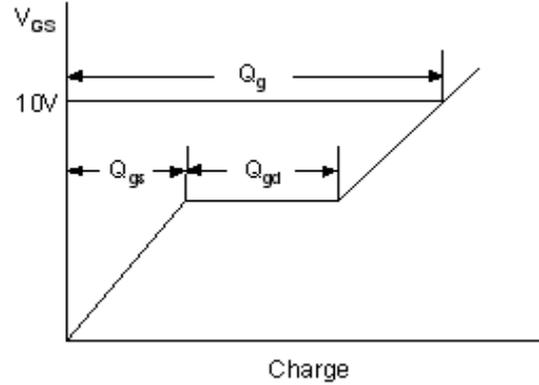
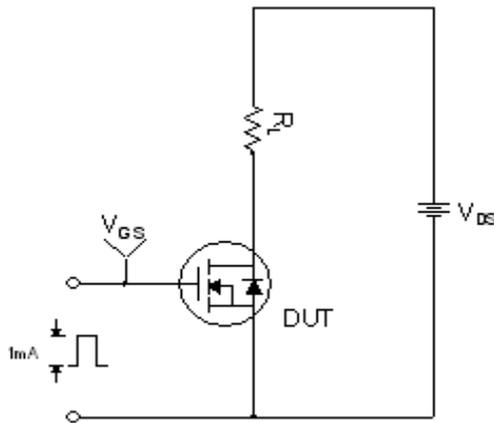


Typical Performance Characteristics

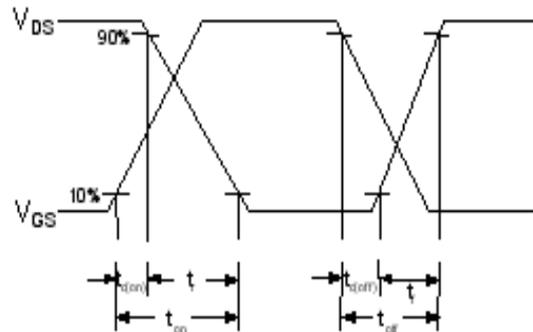
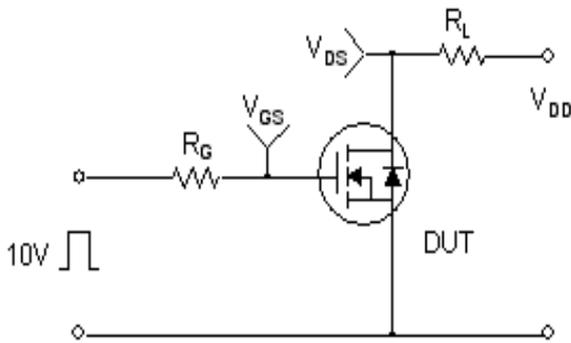
Figure 12. Transient Thermal Response Curve



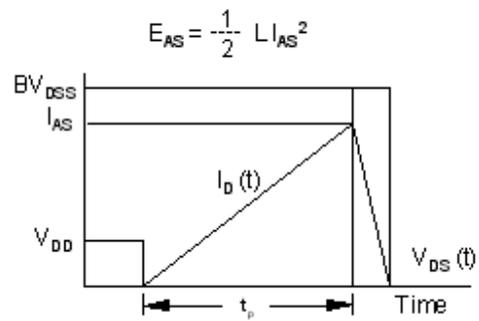
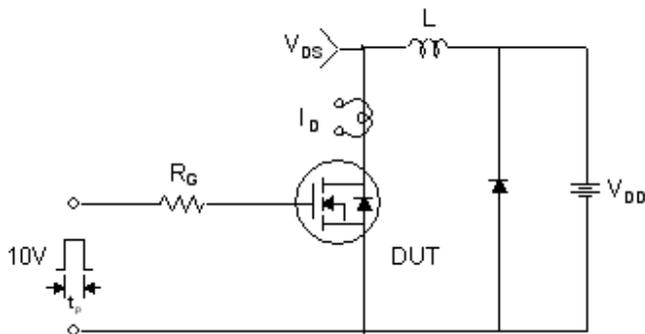
Gate Charge Test Circuit & Waveform



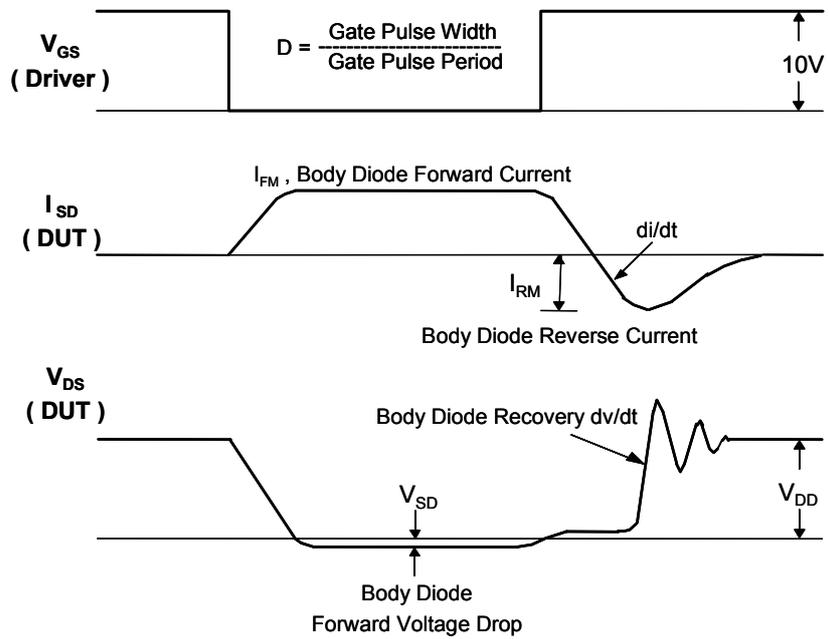
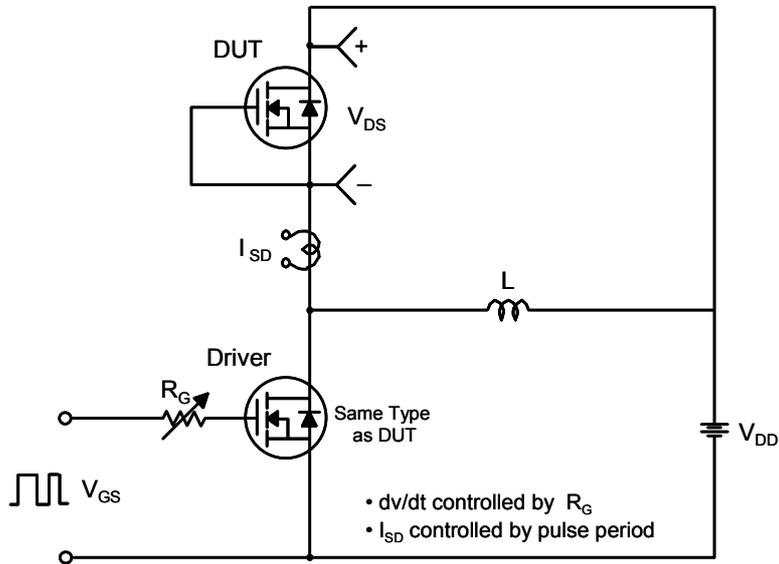
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

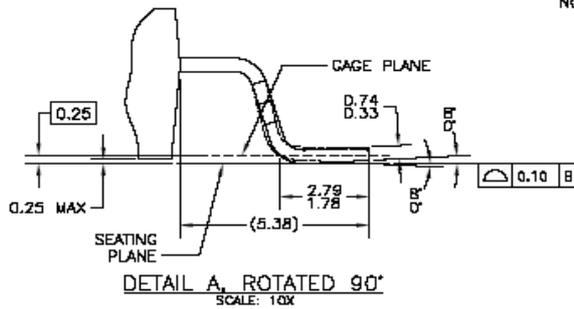
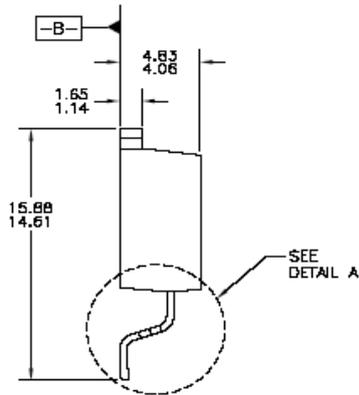
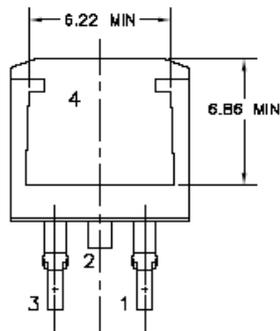
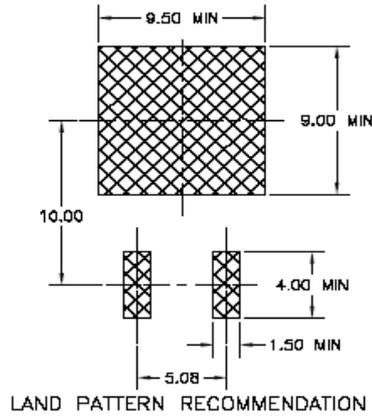
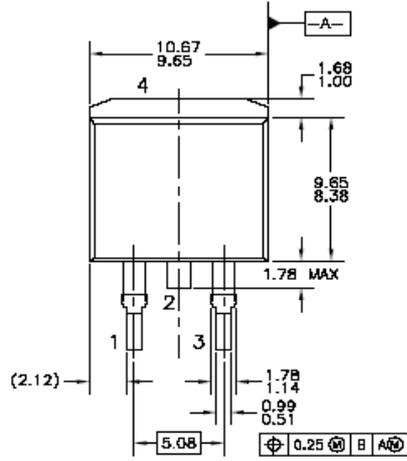


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

D²PAK



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) REFERENCE JEDEC, TO-263, ISSUE D, VARIATION AB, DATED JULY 2003.
 - C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1982.
 - D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
 - E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

T02B3AD2REV0

Dimensions in Millimeters



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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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